

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Collector-emitter voltage BC856S/U BC857S	$V_{CEO}$	65 45	-
Collector-base voltage BC856S, BC856U BC857S	$V_{CBO}$	80 50	V
Emitter-base voltage	$V_{EBO}$	5	
Collector current	$I_C$	100	mA
Peak collector current, $t_p \leq 10$ ms	$I_{CM}$	200	
Total power dissipation- $T_S \leq 115$ °C, BC856S $T_S \leq 118$ °C, BC856U, BC857U	$P_{tot}$	250 250	-
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-65 ... 150	

**Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>1)</sup> BC856S, BC857S BC856U	$R_{thJS}$	$\leq 140$ $\leq 130$	K/W

<sup>1)</sup>For calculation of  $R_{thJA}$  please refer to Application Note AN077 (Thermal Resistance Calculation)

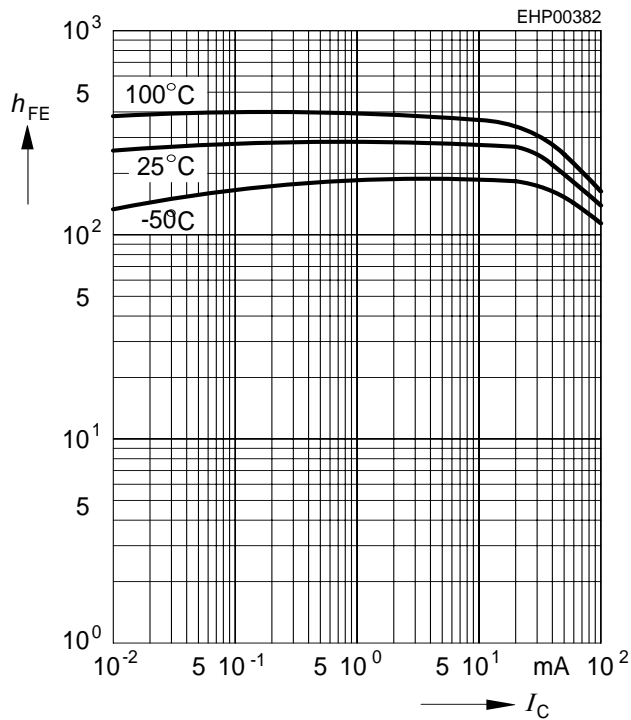
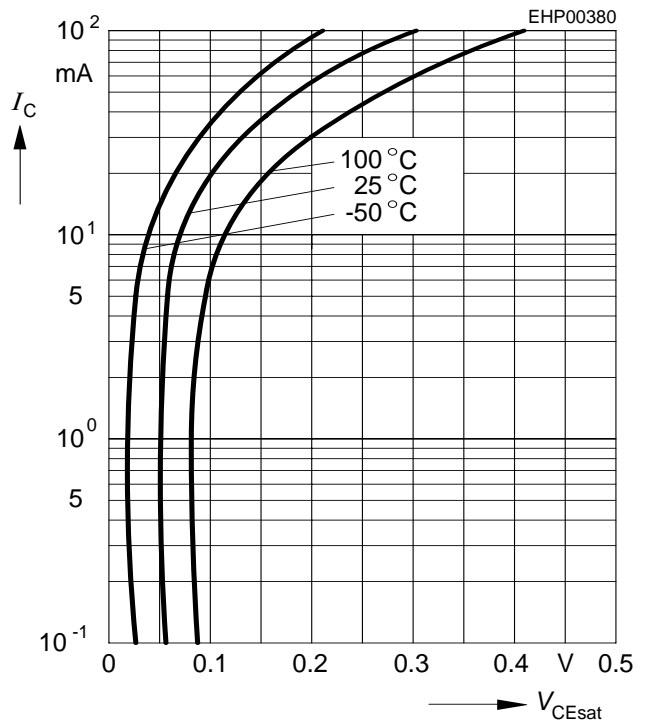
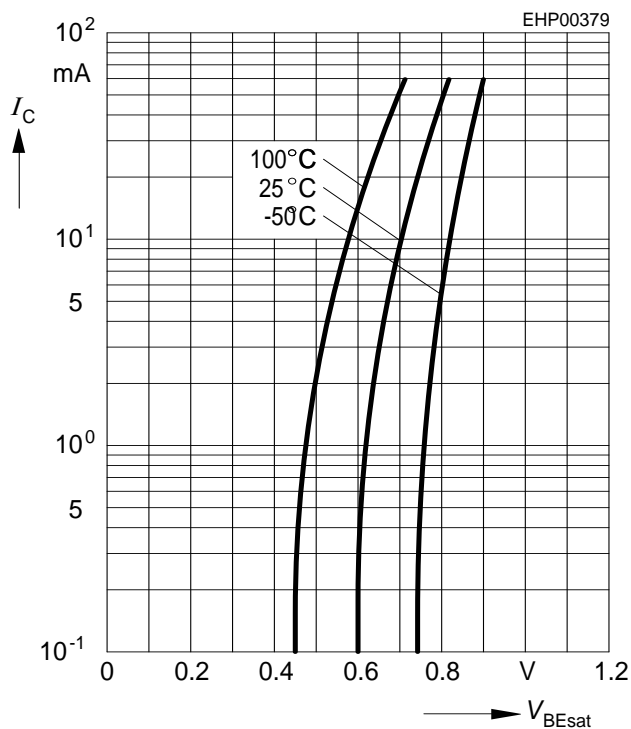
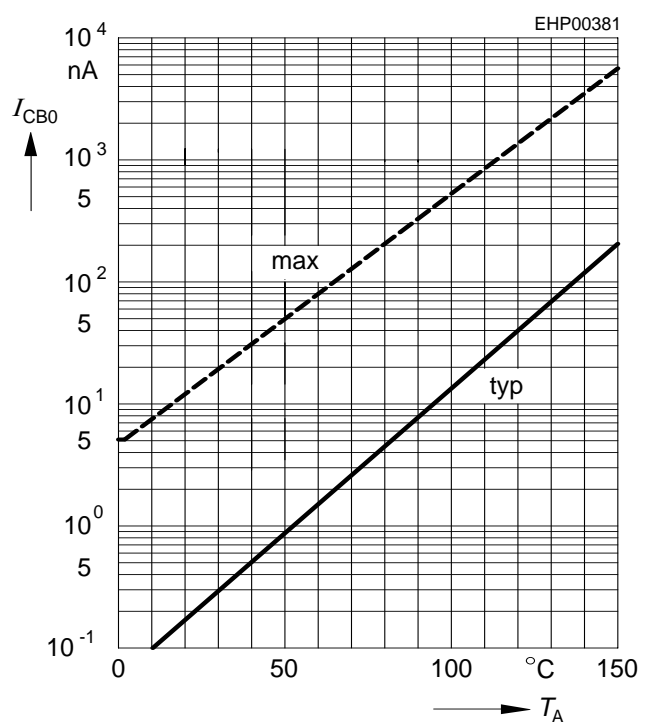
**Electrical Characteristics at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit	
		min.	typ.	max.		
DC Characteristics						
Collector-emitter breakdown voltage $I_C = 10\text{ mA}$ , $I_B = 0$ , BC856S/U $I_C = 10\text{ mA}$ , $I_B = 0$ , BC857S	$V_{(BR)CEO}$	65 45	- -	- -	-	
Collector-base breakdown voltage $I_C = 10\text{ }\mu\text{A}$ , $I_E = 0$ , BC856S/U $I_C = 10\text{ }\mu\text{A}$ , $I_E = 0$ , BC857S	$V_{(BR)CBO}$	80 50	- -	- -		
Emitter-base breakdown voltage $I_E = 10\text{ }\mu\text{A}$ , $I_C = 0$	$V_{(BR)EBO}$	5	-	-		V
Collector-base cutoff current $V_{CB} = 45\text{ V}$ , $I_E = 0$ $V_{CB} = 45\text{ V}$ , $I_E = 0$ , $T_A = 150\text{ }^{\circ}\text{C}$	$I_{CBO}$	- -	- -	0.015 5		$\mu\text{A}$
DC current gain <sup>1)</sup> $I_C = 10\text{ }\mu\text{A}$ , $V_{CE} = 5\text{ V}$ $I_C = 2\text{ mA}$ , $V_{CE} = 5\text{ V}$	$h_{FE}$	- 200	250 290	- 630	-	
Collector-emitter saturation voltage <sup>1)</sup> $I_C = 10\text{ mA}$ , $I_B = 0.5\text{ mA}$ $I_C = 100\text{ mA}$ , $I_B = 5\text{ mA}$	$V_{CEsat}$	- -	75 250	300 650	mV	
Base emitter saturation voltage <sup>1)</sup> $I_C = 10\text{ mA}$ , $I_B = 0.5\text{ mA}$ $I_C = 100\text{ mA}$ , $I_B = 5\text{ mA}$	$V_{BEsat}$	- -	700 850	- -	-	
Base-emitter voltage <sup>1)</sup> $I_C = 2\text{ mA}$ , $V_{CE} = 5\text{ V}$ $I_C = 10\text{ mA}$ , $V_{CE} = 5\text{ V}$	$V_{BE(ON)}$	600 -	650 -	750 820	mV	

<sup>1)</sup>Pulse test:  $t < 300\mu\text{s}$ ;  $D < 2\%$

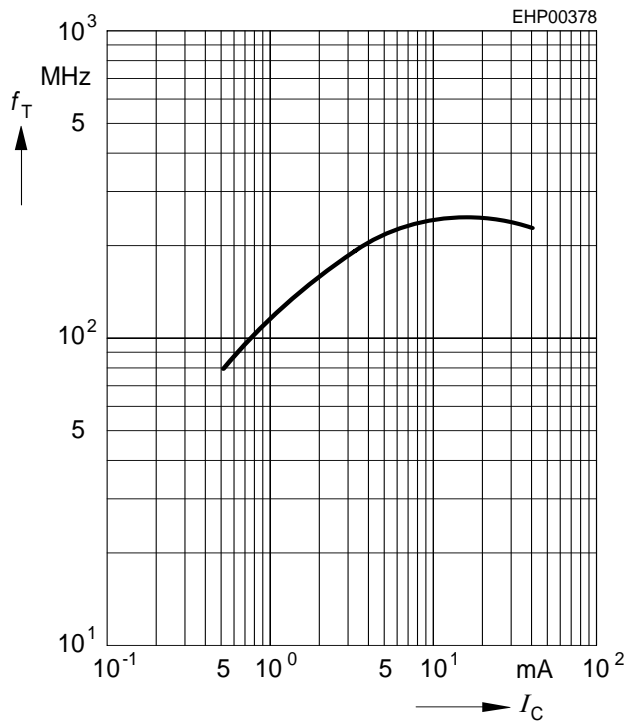
**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Transition frequency $I_C = 20\text{ mA}$ , $V_{CE} = 5\text{ V}$ , $f = 100\text{ MHz}$	$f_T$	-	250	-	MHz
Collector-base capacitance $V_{CB} = 10\text{ V}$ , $f = 1\text{ MHz}$	$C_{cb}$	-	1.5	-	pF
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$ , $f = 1\text{ MHz}$	$C_{eb}$	-	8	-	
Short-circuit input impedance $I_C = 2\text{ mA}$ , $V_{CE} = 5\text{ V}$ , $f = 1\text{ kHz}$	$h_{11e}$	-	4.5	-	kΩ
Open-circuit reverse voltage transf. ratio $I_C = 2\text{ mA}$ , $V_{CE} = 5\text{ V}$ , $f = 1\text{ kHz}$	$h_{12e}$	-	2	-	10 <sup>-4</sup>
Short-circuit forward current transf. ratio $I_C = 2\text{ mA}$ , $V_{CE} = 5\text{ V}$ , $f = 1\text{ kHz}$	$h_{21e}$	-	330	-	-
Open-circuit output admittance $I_C = 2\text{ mA}$ , $V_{CE} = 5\text{ V}$ , $f = 1\text{ kHz}$	$h_{22e}$	-	30	-	μS
Noise figure $I_C = 200\text{ μA}$ , $V_{CE} = 5\text{ V}$ , $f = 1\text{ kHz}$ , $\Delta f = 200\text{ Hz}$ , $R_S = 2\text{ kΩ}$	$F$	-	-	10	dB

**DC current gain  $h_{FE} = f(I_C)$** 
 $V_{CE} = 5 \text{ V}$ 

**Collector-emitter saturation voltage**
 $I_C = f(V_{CEsat}), h_{FE} = 20$ 

**Base-emitter saturation voltage**
 $I_C = f(V_{BEsat}), h_{FE} = 20$ 

**Collector cutoff current  $I_{CBO} = f(T_A)$** 
 $V_{CBO} = 30 \text{ V}$ 


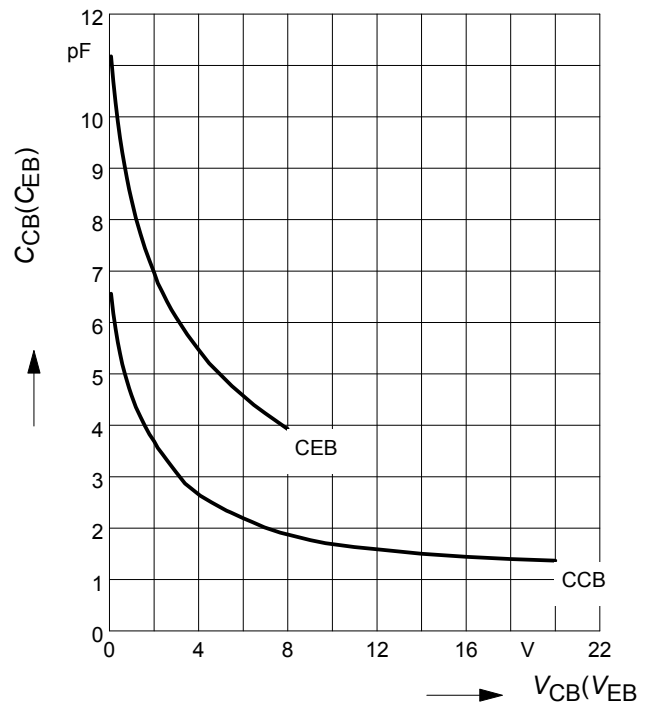
**Transition frequency  $f_T = f(I_C)$**

$V_{CE} = 5\text{ V}$



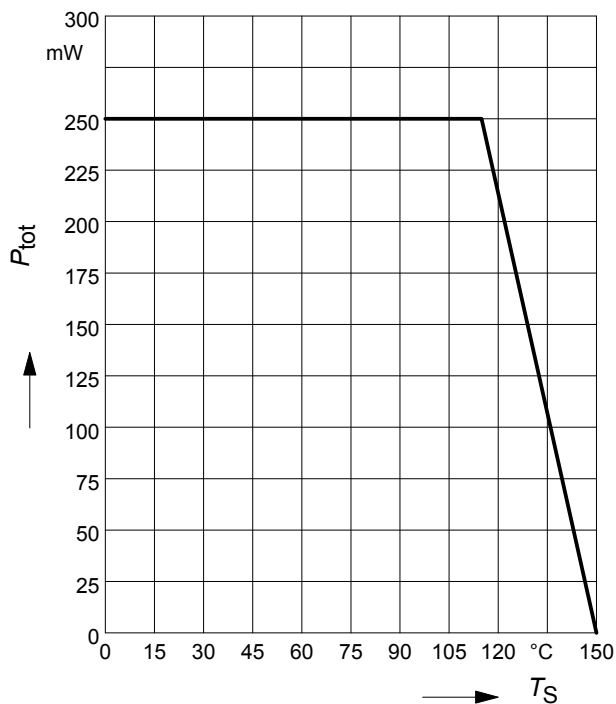
**Collector-base capacitance  $C_{cb} = f(V_{CB})$**

**Emitter-base capacitance  $C_{eb} = f(V_{EB})$**



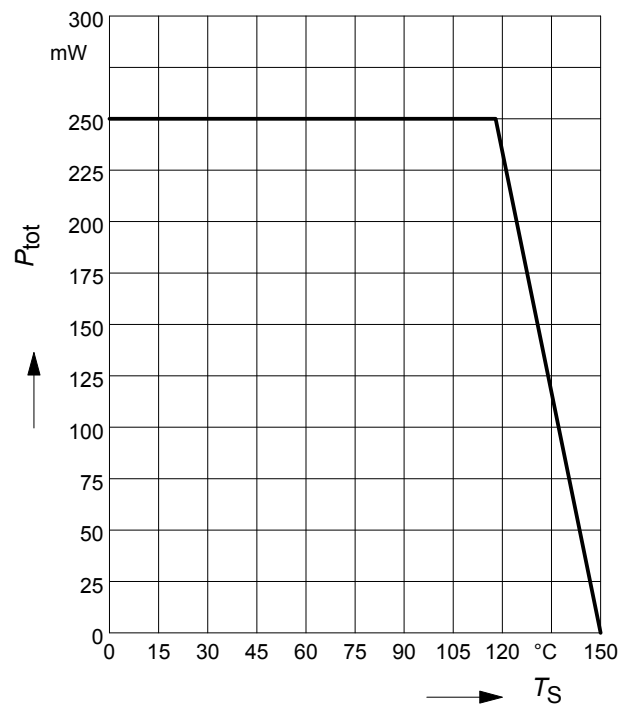
**Total power dissipation  $P_{tot} = f(T_S)$**

BC856S, BC857S



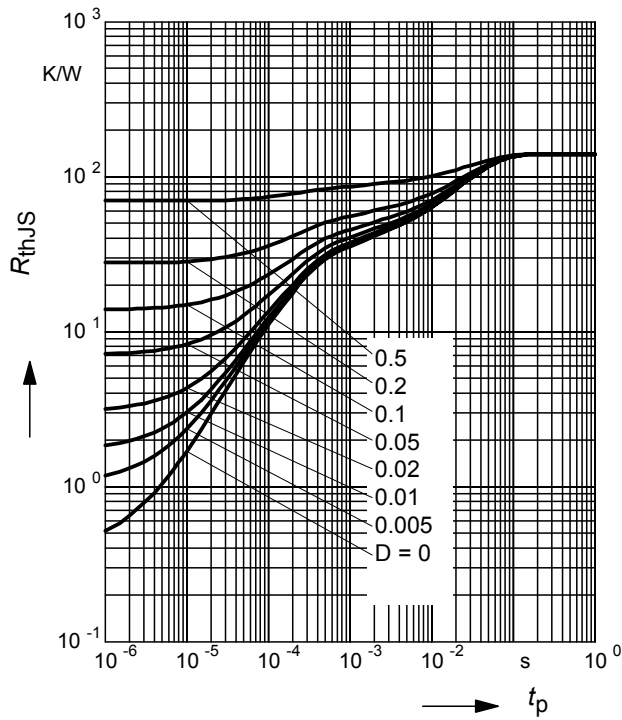
**Total power dissipation  $P_{tot} = f(T_S)$**

BC856U



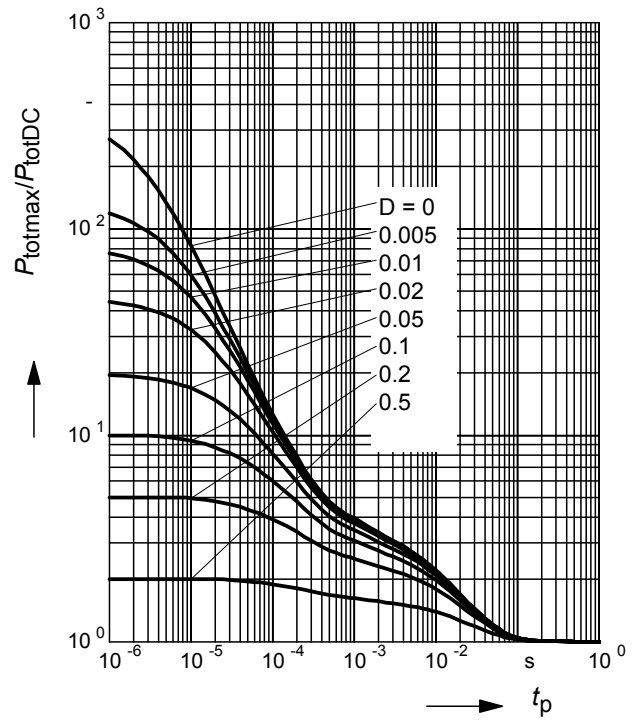
**Permissible Pulse Load  $R_{thJS} = f(t_p)$** 

BC856S; BC857S

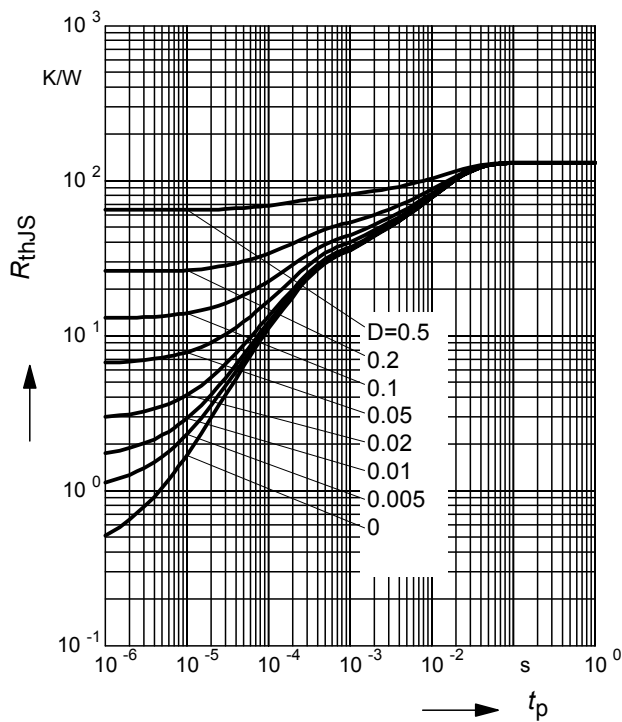

**Permissible Pulse Load**

$$P_{totmax}/P_{totDC} = f(t_p)$$

BC856S, BC857S

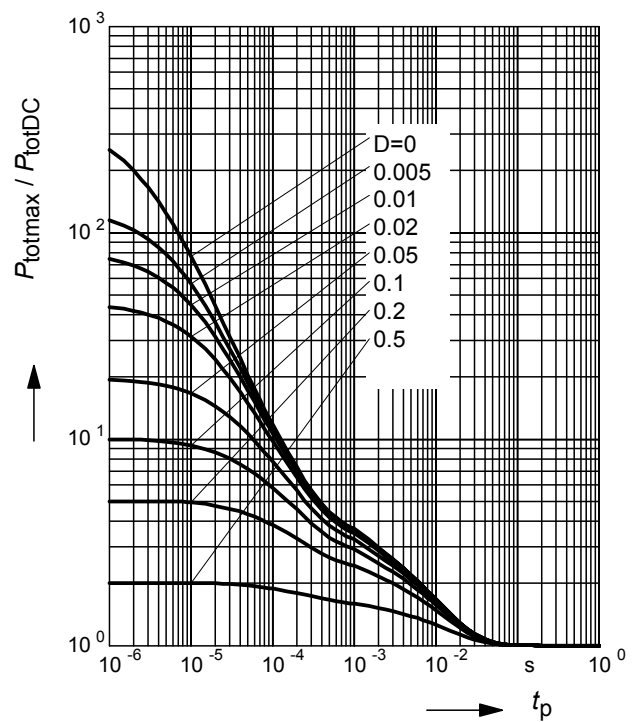

**Permissible Puls Load  $R_{thJS} = f(t_p)$** 

BC856U

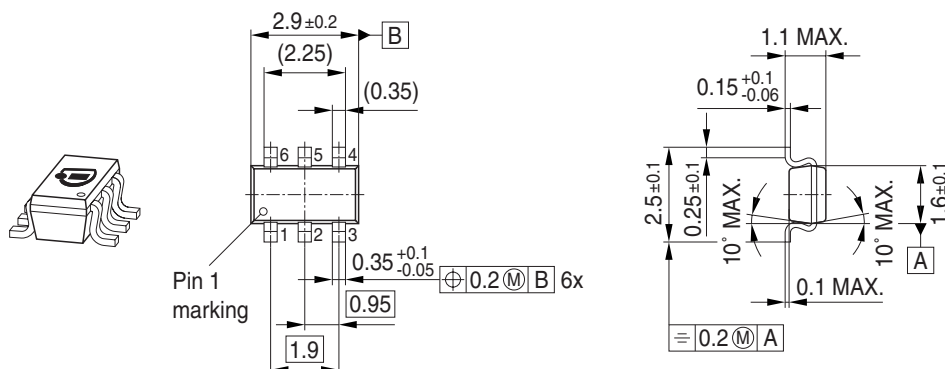

**Permissible Pulse Load**

$$P_{totmax}/P_{totDC} = f(t_p)$$

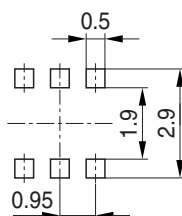
BC856U



## Package Outline

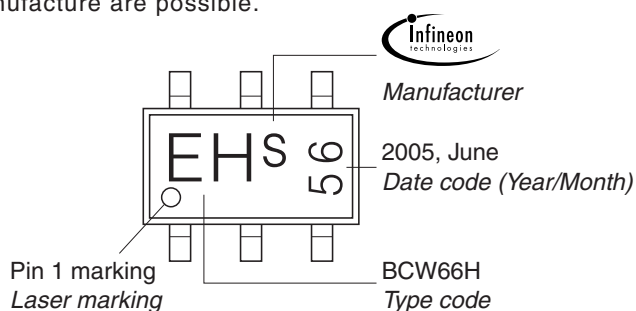


## Foot Print



## Marking Layout (Example)

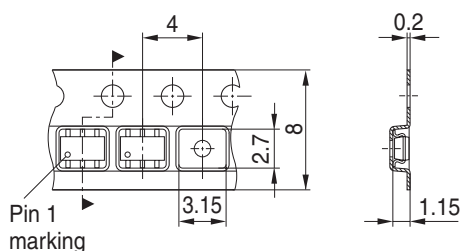
Small variations in positioning of Date code, Type code and Manufacture are possible.



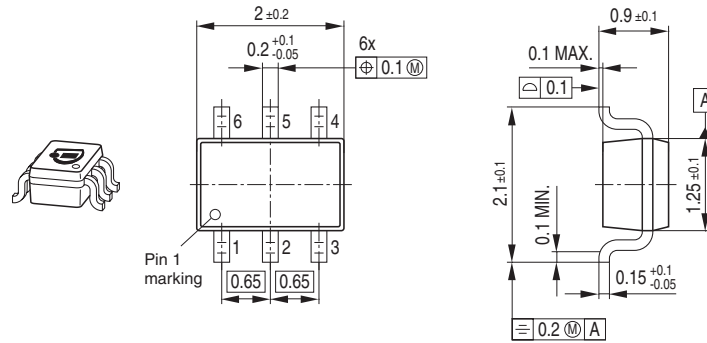
## Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel  
Reel ø330 mm = 10.000 Pieces/Reel

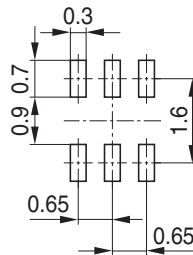
For symmetric types no defined Pin 1 orientation in reel.



## Package Outline

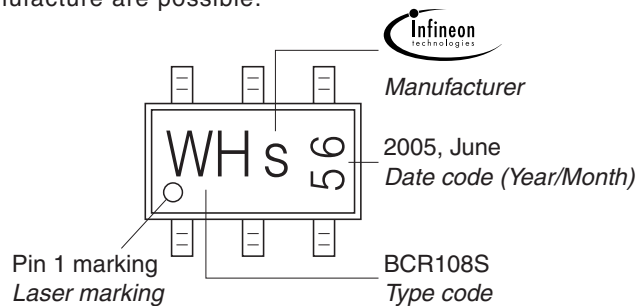


## Foot Print



## Marking Layout (Example)

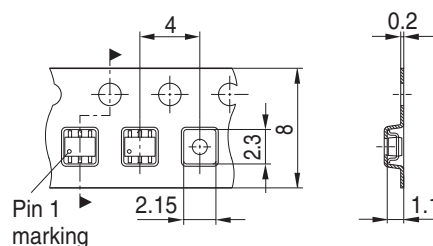
Small variations in positioning of Date code, Type code and Manufacture are possible.



## Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel  
Reel ø330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.





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